



BDY26CZ

NPN SILICON TRANSISTORS, DIFFUSED MESA.

They are NPN transistors mounted in Jedec TO-3.
 LF Large Signal Power Amplification.
 High Current Fast Switching.
 Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings	Value	Unit
V_{CEO}	Collector-Emitter Voltage	220	V
V_{CBO}	Collector-Base Voltage	300	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current	6	A
I_B	Base Current	3	A
P_{TOT}	Power Dissipation @ $T_C = 25^\circ$	87.5	W
T_J	Junction Temperature	200	°C
T_S	Storage Temperature	-65 to +200	

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-C}	Thermal Resistance, Junction to Case	2	°C/W

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

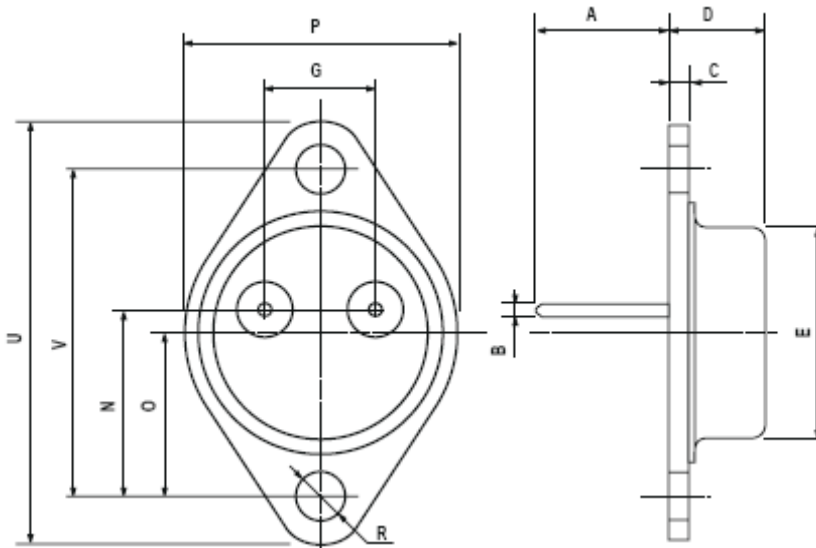
Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
$V_{CEO(BR)}$	Collector-Emitter Breakdown Voltage (*)	$I_C=50\text{ mA}, I_B=0$	220	-	-	V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage (*)	$I_C=3\text{ mA}$	300	-	-	V
I_{CEO}	Collector-Emitter Cutoff Current	$V_{CE}=220\text{ V}$	-	-	1.0	mA
I_{EBO}	Emitter-Base Cutoff Current	$V_{EB}=10\text{ V}$	-	-	1.0	mA
I_{CES}	Collector-Emitter Cutoff Current	$V_{CE}=250\text{ V}$ $V_{BE}=0\text{ V}$	-	-	1.0	mA
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C=2.0\text{ A}, I_B=0.25\text{ A}$	-	-	0.6	V
$V_{BE(SAT)}$	Base-Emitter saturation Voltage (*)	$I_C=2.0\text{ A}, I_B=0.25\text{ A}$	-	-	1.2	V
h_{FE}	Static Forward Current transfer ratio (*)	$V_{CE}=4\text{ V}, I_C=1\text{ A}$	-	90	-	-
		$V_{CE}=4\text{ V}, I_C=2\text{ A}$	75	82	180	
		$V_{CE}=0.5\text{ V}, I_C=250\text{ mA}$	60	-	-	
f_T	Transition Frequency	$V_{CE}=15\text{ V}, I_C=0.5\text{ A}$ $f=10\text{ MHz}$	10	-	-	MHz
$t_d + t_r$	Turn-on time	$I_C=5\text{ A}$ $I_B=1\text{ A}$	-	0.3	0.5	μs
$t_s + t_f$	Turn-off time	$I_C=5\text{ A}$ $I_{B1}=1\text{ A}$ $I_{B2}=-0.5\text{ A}$	-	1.5	2.0	μs

(*) Pulse Width $\approx 300\ \mu\text{s}$, Duty Cycle $\angle 2.0\%$

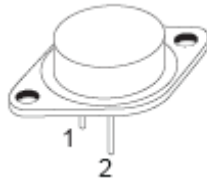
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MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)		
	min	max
A	11	13.10
B	0.97	1.15
C	1.5	1.65
D	8.32	8.92
F	19	20
G	10.70	11.1
N	16.50	17.20
P	25	26
R	4	4.09
U	38.50	39.30
V	30	30.30



Pin 1 :	Base
Pin 2 :	Emitter
Case :	Collector



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